REMARKS

Claims 32-69 are pending in the present application, and claims 33, 34, 36-38 and 62 are under appeal to the Board of Appeals. Claims 32, 35, 39-52, 54-61 and 64-69 have been allowed, and claims 53 and 63 are objected to. Applicants have filed an Appeal Brief on March 21, 2003, and the Examiner's Answer has not been received yet.

The Examiner indicated in the final Office Action mailed on July 5, 2002 that pending claims 53 and 63 would be allowable if rewritten in independent form to include the limitations of the base claim and any intervening claims. Applicants have hereby amended claims 53 and 63 to be in independent form and include the limitations of base claim and any intervening claims. Since the Examiner currently has the jurisdiction of the present application (see MPEP 1210), and since this Amendment merely puts objected-to claims in condition for allowance, Applicants respectfully request entry of this Amendment.

Prompt consideration and allowance of pending claims 53 and 63 are respectfully requested.

The Examiner is invited to contact the undersigned attorney to discuss any matter concerning this application.

The Office is authorized to charge any underpayment or credit any overpayment to Kenyon & Kenyon Deposit Account No. 11-0600.

Respectfully submitted,

Dated: 5/20, 2003

By: [signature] (by [signature] R. No. 36,197)

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MARKED-UP VERSION OF AMENDMENTS

IN THE CLAIMS:

Please amend claims 53 and 63 as follows:

53. (Amended) [The method as recited in claim 33,] A method for etching a silicon layered body, which has a first silicon layer (15) that is provided with an etching mask (10) for defining lateral recesses (21); work with a plasma being carried out in a first etching process, and trenches (21') being formed by anisotropic etching in the region of the lateral recesses (21); at least one separating layer (12, 14, 14', 16) being buried between the first silicon layer (15) and a further silicon layer (17, 17'), and the first etching process coming at least almost to a standstill upon reaching the at least one separating layer; and the separating layer (12, 14, 14', 16) subsequently being etched through in an exposed region (23, 23') by a second etching process, and a third etching process then etching the further silicon layer (17, 17'); wherein a $(CF_2)_n$ film (20) being built up on side walls of the trenches (21') at least one of in the course of the first etching process, prior to the third etching process and during the third etching process; wherein the first and second separating-layer sections (12, 16) are deposited in such manner that the conducting layer (13) is completely enclosed.

63. (Amended) [The method as recited in claim 62,] A method for etching a silicon layered body, which has a first silicon layer (15) that is provided with an etching mask (10) for defining lateral recesses (21); work with a plasma being carried out in a first etching process, and trenches (21') being formed by anisotropic etching in the region of the lateral recesses (21); at least one separating layer (12, 14, 14', 16) being buried between the first silicon layer (15) and a further silicon layer (17, 17'), and the first etching process coming at least almost to a standstill upon reaching the at least one separating layer; and the separating layer (12, 14, 14', 16) subsequently being etched through in an exposed region (23, 23') by a second etching process, and a third etching process then etching the further silicon layer (17, 17'); wherein a $(CF_2)_n$ film (20) being built up on side walls of the trenches (21') at least one of in the course of the first etching process, prior to the third etching process and during the third etching process; wherein the etching mask (10) and the remaining $(CF_2)_n$ films

(20) are finally removed from the etched silicon layered body in an oxygen plasma stripper, using an oxygen ashing process; wherein, after the removal of the remaining $(CF_2)_n$ films, a $(CF_2)_n$ coating is applied to the side walls of the free-standing structure (32), the side walls of the trenches (21'), and all surfaces shadowed by normal ionic incidence, in the course of which electrical contact surfaces, in particular, remain free from a $(CF_2)_n$ coating.